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501.41263X00

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

Applicant(s): NAKABAYASHI et al

Serial No.: 10/091,489

Filed: March 7, 2002

For: Fabrication Method Of Semiconductor Integrated Circuit Device

Group: 2812

Examiner:

**PRELIMINARY AMENDMENT**

Assistant Commissioner for Patents  
Washington, D.C. 20231

April 22, 2002

Sir:

The following preliminary amendments and remarks are respectfully submitted in connection with the above-identified application.

**IN THE SPECIFICATION:**

Please replace the original specification with the attached Substitute Specification.

**IN THE ABSTRACT OF THE DISCLOSURE:**

Please replace the original abstract with the attached abstract.

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## ABSTRACT OF THE DISCLOSURE

In order to reduce micro scratches which tend to occur during chemical-mechanical polishing, a polishing slurry is diluted with deionized water immediately before it is supplied in a gap between a polishing pad and the surface of a wafer to be polished. By diluting the polishing slurry with deionized water to increase its volume, the concentration of coagulated particles contained in the polishing slurry can be lowered. For a mixture ratio of the polishing slurry and deionized water, about 1 (polishing slurry): 1 - 1.2 (deionized water) is used, and the concentration of silica contained in the diluted polishing slurry is adjusted to about 3 - 9 weight %, preferably about 4 - 8 weight %, and more preferably about 8 weight %.

**REMARKS**

The specification has been amended to correct errors of a typographical and grammatical nature. Due to the number of corrections thereto, applicants submit herewith a Substitute Specification, along with a marked-up copy of the original specification for the Examiner's convenience. The substitute specification includes the changes as shown in the marked-up copy and includes no new matter. Therefore, entry of the Substitute Specification is respectfully requested.

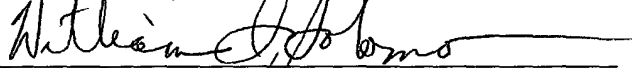
The abstract has also been amended to more clearly describe the features of the present invention.

Entry of the preliminary amendments and examination of the application is respectfully requested.

To the extent necessary, applicant's petition for an extension of time under 37 CFR 1.136. Please charge any shortage in the fees due in connection with the filing of this paper, including extension of time fees, to Deposit Account No. 01-2135 (501.41263X00) and please credit any excess fees to such deposit account.

Respectfully submitted,

ANTONELLI, TERRY, STOUT & KRAUS, LLP



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REWRITTEN MARKED UP COPYIN THE ABSTRACT:

~~The subject of the present invention is~~ In order to reduce micro scratches ~~by applying~~  
~~which tend to occur during~~ chemical-mechanical polishing. ~~A~~, a polishing slurry is diluted  
with deionized water immediately before it is supplied in a gap between a polishing pad and  
the surface of a wafer to be polished ~~of a wafer~~. By diluting the polishing slurry with  
deionized water to increase its volume, the concentration of coagulated particles contained in  
the polishing slurry can be lowered. For a mixture ratio of the polishing slurry and deionized  
water, about 1 (polishing slurry): 1 - 1.2 (deionized water) is used, and the concentration of  
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